

Supplemental Materials

Tailoring Electronic and Thermoelectric Properties of The SnSe Monolayer via Vacancy Defects: Insights from Density Functional Theory

Erik Bhekti Yutomo ^a, Suci Faniandari ^a, Muhammad Fahmi ^a

^a Department of Physics, Faculty of Science and Mathematics, Diponegoro University,
Semarang, 50275, Indonesia.

Corresponding author: erikbhekti@fisika.fsm.undip.ac.id

S1. k-point Convergence Test

To verify the reliability and accuracy of the DFT calculations, a k-point convergence test was carried out for the monolayer SnSe system. The total energy was calculated using different Monkhorst–Pack grids ranging from $2 \times 2 \times 1$ to $10 \times 10 \times 1$. As shown in Figure S1, the variation of total energy becomes negligible beyond the $7 \times 7 \times 1$ grid, where the difference in total energy compared to $8 \times 8 \times 1$ is less than 1 meV/atom. Therefore, the $7 \times 7 \times 1$ k-point grid was selected for all subsequent calculations of perfect and defected SnSe monolayers to ensure a good balance between computational accuracy and efficiency.

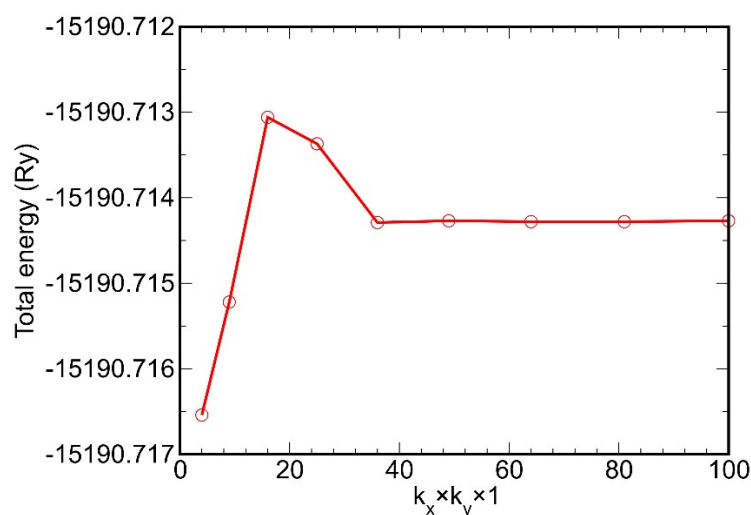


Figure S1. Total energy (in Ry) of the SnSe monolayer as a function of k-point mesh density ($k_x \times k_y \times 1$) obtained using the Monkhorst–Pack scheme. The total energy becomes nearly constant beyond the $7 \times 7 \times 1$ grid, indicating convergence of the Brillouin zone sampling.

S2. Normalized Transport Coefficients.

To complement the discussion of thermoelectric transport properties, the normalized electrical conductivity (σ/τ) and electronic thermal conductivity (κ_e/τ) were calculated as functions of the chemical potential (μ_{chem}) for all monolayer systems (SnSe, $\text{Sn}_{0.94}\text{Se}$, $\text{SnSe}_{0.94}$, and $\text{Sn}_{0.94}\text{Se}_{0.94}$) at 300 K. These quantities allow the intrinsic electronic transport behavior to be analyzed without the influence of the absolute value of relaxation time (τ) derived from potential deformation theory. The σ/τ and κ_e/τ curves exhibit consistent trends, indicating that the variations in electrical and electronic thermal transport are primarily governed by the electronic structure modifications induced by vacancies. Furthermore, the correlation between σ/τ and κ_e/τ confirms that the Wiedemann–Franz relationship remains valid across all considered systems.

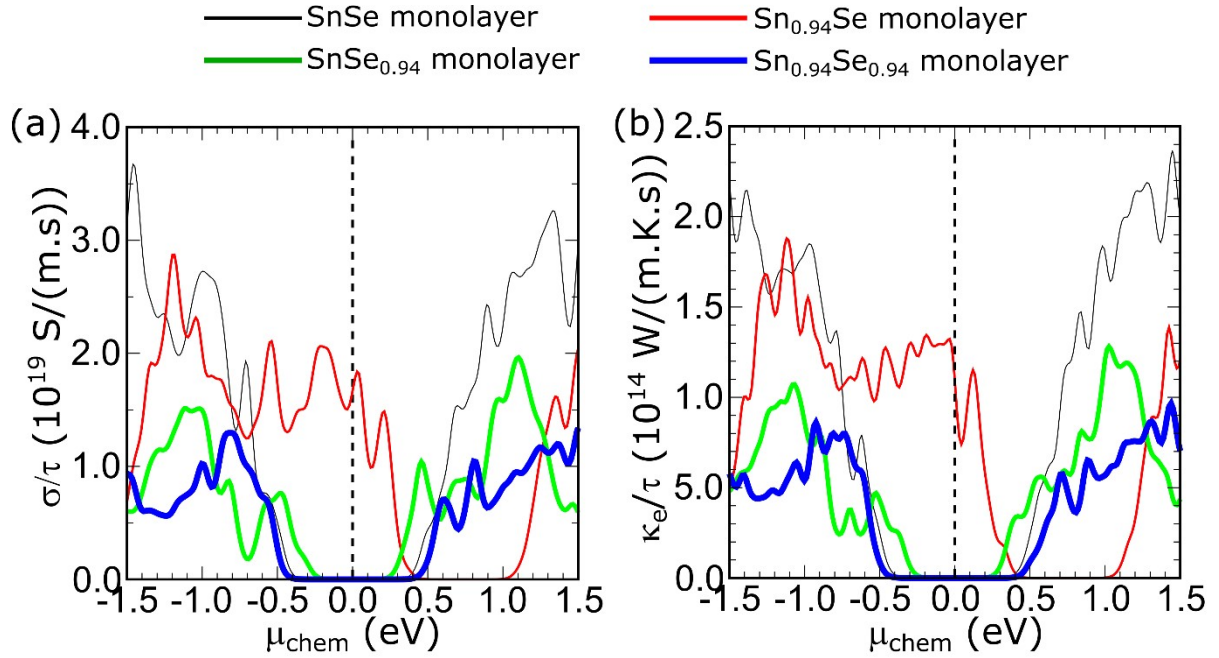


Figure S2. Normalized (a) electrical conductivity (σ/τ) and (b) electronic thermal conductivity (κ_e/τ) as a function of μ_{chem} for the SnSe, $\text{Sn}_{0.94}\text{Se}$, $\text{SnSe}_{0.94}$, and $\text{Sn}_{0.94}\text{Se}_{0.94}$ monolayers at 300 K.